

AMENDMENTS TO THE SPECIFICATION:

Please amend the Substitute Specification submitted with the Preliminary Amendment filed November 27, 2001, as follows:

Please delete paragraph [0021] on page 8 of the above-mentioned Substitute Specification, and substitute therefor the following new paragraph:

--(5) A method of fabricating a semiconductor integrated circuit device having MISFETs formed on the main surface of a semiconductor substrate, includes the steps of: (a) forming a gate insulating film on said semiconductor substrate; (b) forming a gate electrode with a width of 0.18 μm or below by patterning the silicon film deposited on said gate insulating film; (c) forming the source/drain regions on both sides of said gate electrode by injecting impurities into the semiconductor substrate, (d) sputter-etching away the top of said source/drain regions to 2.5 nm or less below the surface of the regions; (e) then, under near-vacuum conditions and in the same apparatus in which said sputter etching was carried out, forming a metal film on said source/drain regions; (f) forming a metallic silicide layer with sheet resistance of $\underline{5\Omega/\square}$ ~~5- Ω/\square~~ to $\underline{12\Omega/\square}$ ~~12- Ω/\square~~ , where said source/drain regions are in contact with said metal film; and (g) removing said metal film which did not react in step (f).--